# 2SA1739

### Silicon PNP epitaxial planar type

For high speed switching Complementary to 2SC3938

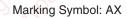
#### Features

- High speed switching
- $\bullet$  Low collector-emitter saturation voltage  $V_{\mbox{CE(sat)}}$
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

		Unit: mm
0.3±0.1	(0.425)	0.15+0.10
1 2 1 (0.65), (0.65), 1.3±0.1 2.0±0.2	2.1±0.1	0 0 0 0 0 0 0 0 0
	0 to 0.1 0.9±0.1 0.9 <sup>±0.2</sup>	1: Base 2: Emitter 3: Collector EIAJ: SC-70 SMini3-G1 Package

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-15	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-15	V	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	-4	V	
Collector current	I <sub>C</sub>	-50	mA	
Peak collector current	I <sub>CP</sub>	-100	mA	
Collector power dissipation	P <sub>C</sub>	150	mW	
Junction temperature	Tj	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	



#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -8 V, I_E = 0$	<i>X</i> 2	S	- 0.1	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{CE} = -3 V, I_C = 0$	- A		- 0.1	μΑ
Forward current transfer ratio	h <sub>FE1</sub> *	$V_{CE} = -1 V, I_C = -10 mA$	50		150	
	h <sub>FE2</sub>	$V_{CE} = -1 V, I_C = -1 mA$	30			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -1 \text{ mA}$		- 0.1	- 0.2	V
Transition frequency	f <sub>T</sub>	$V_{CB} = -10 \text{ V}, I_E = 10 \text{ mA}, f = 200 \text{ MHz}$	800	1 500		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = -5 V, I_E = 0, f = 1 MHz$		1		pF
Turn-on time	t <sub>on</sub>	Refer to the switching time		12		ns
Turn-off time	t <sub>off</sub>	measurement circuit		20		ns
Storage time	t <sub>stg</sub>			19		ns

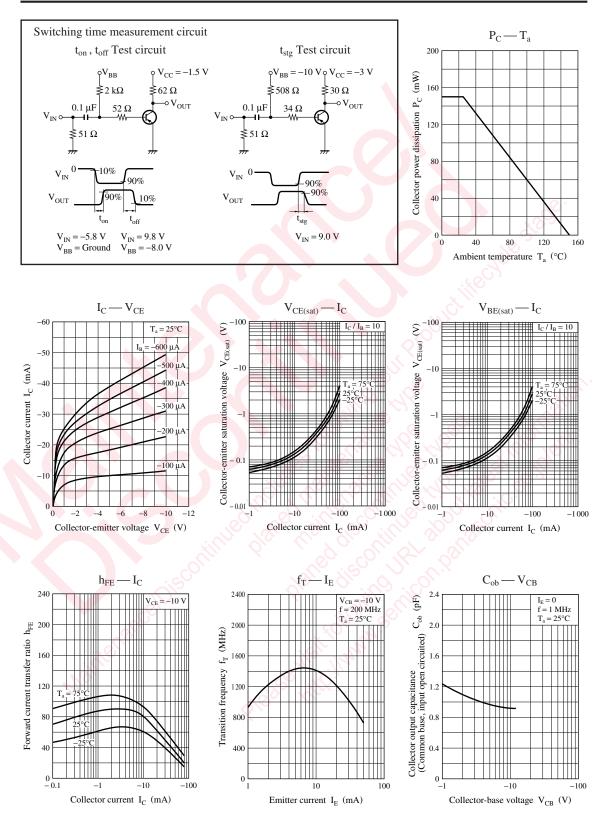
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*: Rank classification

Rank	Q	R	No-rank		
h <sub>FE1</sub>	50 to 120	90 to 150	50 to 150		
Marking symbol	AXQ	AXR	AX		

Product of no-rank is not classified and have no marking symbol for rank.

## Panasonic



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